Programmable Precision References

The TL431, A, B integrated circuits are three–terminal programmable shunt regulator diodes. These monolithic IC voltage references operate as a low temperature coefficient zener which is programmable from V_{ref} to 36 V with two external resistors. These devices exhibit a wide operating current range of 1.0 mA to 100 mA with a typical dynamic impedance of 0.22 Ω . The characteristics of these references make them excellent replacements for zener diodes in many applications such as digital voltmeters, power supplies, and op amp circuitry. The 2.5 V reference makes it convenient to obtain a stable reference from 5.0 V logic supplies, and since the TL431, A, B operates as a shunt regulator, it can be used as either a positive or negative voltage reference.

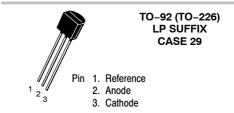
Features

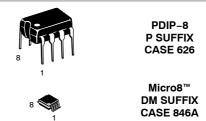
- Programmable Output Voltage to 36 V
- Voltage Reference Tolerance: ±0.4%, Typ @ 25°C (TL431B)
- Low Dynamic Output Impedance, 0.22 Ω Typical
- Sink Current Capability of 1.0 mA to 100 mA
- Equivalent Full-Range Temperature Coefficient of 50 ppm/°C Typical
- Temperature Compensated for Operation over Full Rated Operating Temperature Range
- Low Output Noise Voltage
- These are Pb-Free and Halide-Free Devices

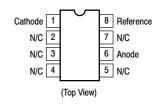


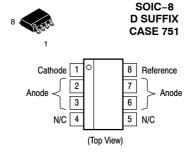
ON Semiconductor®

http://onsemi.com









This is an internally modified SOIC–8 package. Pins 2, 3, 6 and 7 are electrically common to the die attach flag. This internal lead frame modification increases power dissipation capability when appropriately mounted on a printed circuit board. This modified package conforms to all external dimensions of the standard SOIC–8 package.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 13 of this data sheet.

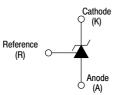
DEVICE MARKING INFORMATION

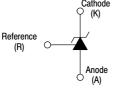
See general marking information in the device marking section on page 14 of this data sheet.

Symbol

Representative Schematic Diagram

Component values are nominal





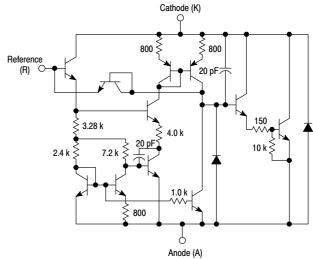
Representative Block Diagram

Anode (A)

2.5 V_{ref}

Reference

(R)



This device contains 12 active transistors.

MAXIMUM RATINGS (Full operating ambient temperature range applies, unless otherwise noted.)

Cathode

Rating	Symbol	Value	Unit
Cathode to Anode Voltage	V _{KA}	37	V
Cathode Current Range, Continuous	lκ	-100 to +150	mA
Reference Input Current Range, Continuous	I _{ref}	-0.05 to +10	mA
Operating Junction Temperature	TJ	150	°C
Operating Ambient Temperature Range TL431I, TL431AI, TL431BI TL431C, TL431AC, TL431BC NCV431AI, NCV431B, TL431BV	T _A	-40 to +85 0 to +70 -40 to +125	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C Ambient Temperature D, LP Suffix Plastic Package P Suffix Plastic Package DM Suffix Plastic Package	P _D	0.70 1.10 0.52	W
Total Power Dissipation @ T _C = 25°C Derate above 25°C Case Temperature D, LP Suffix Plastic Package P Suffix Plastic Package	P _D	1.5 3.0	W
ESD Rating	HBM MM	>2000 >200	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Condition	Symbol	Min	Max	Unit
Cathode to Anode Voltage	V_{KA}	V_{ref}	36	V
Cathode Current	I _K	1.0	100	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	D, LP Suffix Package	P Suffix Package	DM Suffix Package	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	178	114	240	°C/W
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	83	41	-	°C/W

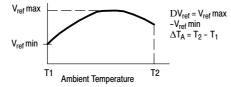
ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted.)

			TL431I		TL431C			
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Reference Input Voltage (Figure 1) $V_{KA} = V_{ref}, I_K = 10 \text{ mA}$ $T_A = 25^{\circ}\text{C}$ $T_A = T_{low} \text{ to } T_{high} \text{ (Note 1)}$	V _{ref}	2.44 2.41	2.495 -	2.55 2.58	2.44 2.423	2.495 -	2.55 2.567	V
Reference Input Voltage Deviation Over Temperature Range (Figure 1, Notes 1, 2) V _{KA} = V _{ref} , I _K = 10 mA	ΔV_{ref}	_	7.0	30	_	3.0	17	mV
Ratio of Change in Reference Input Voltage to Change in Cathode to Anode Voltage $I_K = 10$ mA (Figure 2), $\Delta V_{KA} = 10$ V to V_{ref} $\Delta V_{KA} = 36$ V to 10 V	$rac{\Delta V_{ m ref}}{\Delta V_{ m KA}}$	- -	-1.4 -1.0	-2.7 -2.0	- -	-1.4 -1.0	-2.7 -2.0	mV/V
Reference Input Current (Figure 2) $I_K = 10 \text{ mA, } R1 = 10 \text{ k, } R2 = \infty$ $T_A = 25^{\circ}\text{C}$ $T_A = T_{low} \text{ to } T_{high} \text{ (Note 1)}$	l _{ref}	- -	1.8	4.0 6.5	- -	1.8 -	4.0 5.2	μΑ
Reference Input Current Deviation Over Temperature Range (Figure 2, Note 1, 4) I _K = 10 mA, R1 = 10 k, R2 = ∞	ΔI_{ref}	_	0.8	2.5	-	0.4	1.2	μΑ
Minimum Cathode Current For Regulation V _{KA} = V _{ref} (Figure 1)	I _{min}	-	0.5	1.0	-	0.5	1.0	mA
Off–State Cathode Current (Figure 3) V _{KA} = 36 V, V _{ref} = 0 V	I _{off}	-	20	1000	-	20	1000	nA
Dynamic Impedance (Figure 1, Note 3) $V_{KA} = V_{ref}, \Delta I_K = 1.0 \text{mA to 100 mA} \\ f \leq 1.0 \text{kHz}$	Z _{KA}	-	0.22	0.5		0.22	0.5	Ω

1. T_{low} = -40° C for TL431AIP TL431AILP, TL431IP, TL431BID, TL431BID, TL431BID, TL431BIDM, TL431AIDM, TL431BIDM, TL431ACDM, TL431ACDM, TL431ACDM, TL431BCDM, TL431BCDM

 $\begin{array}{lll} T_{high} &=& +85^{\circ}\text{C} \;\; \text{for} \;\; \text{TL431AIP,} \;\; \text{TL431IP,} \;\; \text{TL431IP,} \;\; \text{TL431BID,} \;\; \text{TL431BIP,} \;\; \text{TL431BIDM,} \;\; \text{TL431BIDM,} \;\; \text{TL431BIDM,} \;\; \text{TL431BIDM,} \;\; \text{TL431BCDM,} \;\; \text{TL431BCM,} \;\; \text{T$

 The deviation parameter ΔV_{ref} is defined as the difference between the maximum and minimum values obtained over the full operating ambient temperature range that applies.



The average temperature coefficient of the reference input voltage, $\alpha \text{V}_{\text{ref}}$ is defined as:

$$V_{ref} \stackrel{ppm}{\overset{\circ}{C}} = \frac{\left(\frac{\Delta V_{ref}}{V_{ref} \stackrel{\textcircled{@}}{@} 25 \stackrel{\circ}{C}}\right) X 10^{6}}{\Delta T_{A}} = \frac{\Delta V_{ref} \times 10^{6}}{\Delta T_{A} (V_{ref} \stackrel{\textcircled{@}}{@} 25 \stackrel{\circ}{C})}$$

 αV_{ref} can be positive or negative depending on whether V_{ref} Min or V_{ref} Max occurs at the lower ambient temperature. (Refer to Figure 6.)

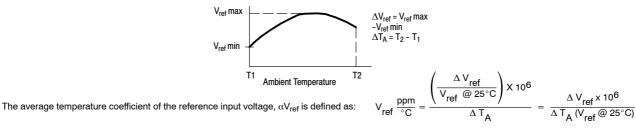
Example :
$$\Delta V_{ref} = 8.0 \text{ mV}$$
 and slope is positive, $V_{ref} @ 25^{\circ}C = 2.495 \text{ V}, \Delta T_{A} = 70^{\circ}C$ $\alpha V_{ref} = \frac{0.008 \times 10^{6}}{70 \text{ (2.495)}} = 45.8 \text{ ppm/}^{\circ}C$

3. The dynamic impedance Z_{KA} is defined as: $|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$. When the device is programmed with two external resistors, R1 and R2, (refer to Figure 2) the total dynamic impedance of the circuit is defined as: $|Z_{KA}'| \approx |Z_{KA}| \left(1 + \frac{R1}{R2}\right)$

ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted.)

		TL431AI / NCV431AI		TL431AI / NCV431AI TL431A0		5	TI	BC / TL4 L431BV CV431B	/		
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
Reference Input Voltage (Figure 1) $V_{KA} = V_{ref}, I_K = 10 \text{ mA}$ $T_A = 25^{\circ}\text{C}$ $T_A = T_{low} \text{ to } T_{high}$	V _{ref}	2.47 2.44	2.495 –	2.52 2.55	2.47 2.453	2.495 -	2.52 2.537	2.485 2.475	2.495 2.495	2.505 2.515	V
Reference Input Voltage Deviation Over Temperature Range (Figure 1, Notes 4, 5) V _{KA} = V _{ref} , I _K = 10 mA	ΔV_{ref}	_	7.0	30	-	3.0	17	-	3.0	17	mV
Ratio of Change in Reference Input Voltage to Change in Cathode to Anode Voltage $I_K = 10$ mA (Figure 2), $\Delta V_{KA} = 10$ V to V_{ref} $\Delta V_{KA} = 36$ V to 10 V	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	- -	-1.4 -1.0	-2.7 -2.0	- -	-1.4 -1.0	-2.7 -2.0	- -	-1.4 -1.0	-2.7 -2.0	mV/V
Reference Input Current (Figure 2) $I_K = 10$ mA, R1 = 10 k, R2 = ∞ $T_A = 25^{\circ}C$ $T_A = T_{low}$ to T_{high} (Note 4)	I _{ref}	- -	1.8 -	4.0 6.5	- -	1.8	4.0 5.2	_ _	1.1	2.0 4.0	μΑ
Reference Input Current Deviation Over Temperature Range (Figure 2, Note 4) I _K = 10 mA, R1 = 10 k, R2 = ∞	ΔI_{ref}	-	0.8	2.5	-	0.4	1.2	-	0.8	2.5	μΑ
	I _{min}	-	0.5	1.0	-	0.5	1.0	-	0.5	1.0	mA
Off–State Cathode Current (Figure 3) V _{KA} = 36 V, V _{ref} = 0 V	l _{off}	_	20	1000	_	20	1000	_	0.23	500	nA
Dynamic Impedance (Figure 1, Note 6) $V_{KA} = V_{ref}$, $\Delta I_{K} = 1.0$ mA to 100 mA f ≤ 1.0 kHz	Z _{KA}	_	0.22	0.5	-	0.22	0.5	-	0.14	0.3	Ω

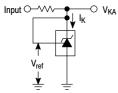
- 4. T_{low} = -40°C for TL431AIP TL431AILP, TL431IP, TL431BID, TL431BIP, TL431BILP, TL431BILP, TL431BIDM, TL43BIDM, TL43BIDM TL431BIDM, NCV431AIDMR2G, NCV431AIDR2G, NCV431BVDR2G
 - 0°C for TL431ACP, TL431ACLP, TL431CP, TL431CD, TL431CD, TL431ACD, TL431BCD, TL431BCP, TL431BCLP, TL431CDM, TL431ACDM, TL431BCDM
 - $T_{high} = +85^{\circ}\text{C for TL431AIP, TL431IP, TL431IP, TL431BID, TL431BIP, TL431BIP, TL431BIP, TL431BIP, TL431BIP, TL431BCP, TL431BCP, TL431ACP, TL431ACDM, TL431ACM, TL431ACM, TL431ACM, TL431ACM, TL431ACM, TL431ACM, TL431ACM, TL431ACM, TL431ACM, TL431A$ TL431BCDM
 - = +125°C TL431BV, NCV431AIDMR2G, NCV431AIDR2G, NCV431BVDMR2G, NCV431BVDR2G
- 5. The deviation parameter ΔV_{ref} is defined as the difference between the maximum and minimum values obtained over the full operating ambient temperature range that applies.

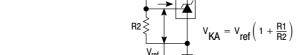


 αV_{ref} can be positive or negative depending on whether V_{ref} Min or V_{ref} Max occurs at the lower ambient temperature. (Refer to Figure 6.)

$$\begin{aligned} \text{Example} : \Delta \text{V}_{ref} &= 8.0 \text{ mV and slope is positive,} \\ \text{V}_{ref} &@ 25^{\circ}\text{C} &= 2.495 \text{ V}, \Delta \text{T}_{\text{A}} &= 70^{\circ}\text{C} \end{aligned} \qquad \alpha \text{ V}_{ref} &= \frac{0.008 \times 10^6}{70 \ (2.495)} = 45.8 \text{ ppm/}^{\circ}\text{C} \end{aligned}$$

- 6. The dynamic impedance Z_{KA} is defined as $|Z_{KA}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$ When the device is programmed with two external resistors, R1 and R2, (reference)
- to Figure 2) the total dynamic impedance of the circuit is defined as: $|Z_{KA}'| \approx |Z_{KA}| \left(1 + \frac{R1}{R2}\right)$ 7. NCV431AIDMR2G, NCV431BVDMR2G, NCV431BVDMR2G, NCV431BVDR2G $T_{low} = -40^{\circ}\text{C}$, $T_{high} = +125^{\circ}\text{C}$. Guaranteed by design. NCV prefix is for automotive and other applications requiring unique site and control change requirements.





Input O

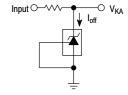


Figure 1. Test Circuit for $V_{KA} = V_{ref}$

Figure 2. Test Circuit for $V_{KA} > V_{ref}$

Figure 3. Test Circuit for Ioff

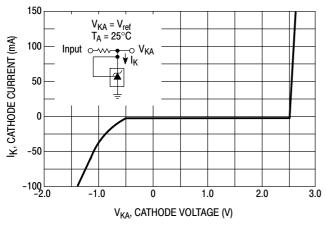


Figure 4. Cathode Current versus Cathode Voltage

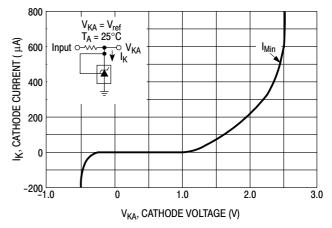


Figure 5. Cathode Current versus Cathode Voltage

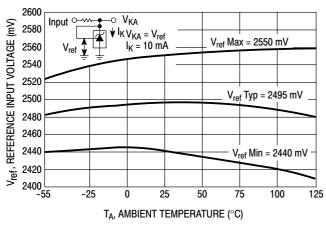


Figure 6. Reference Input Voltage versus Ambient Temperature

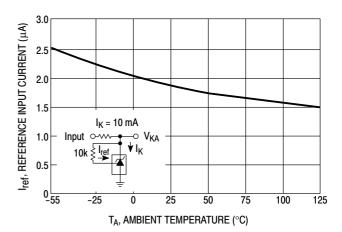


Figure 7. Reference Input Current versus
Ambient Temperature

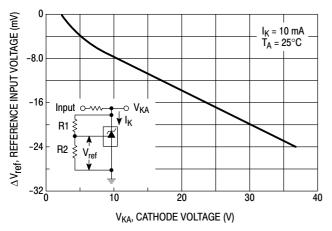


Figure 8. Change in Reference Input Voltage versus Cathode Voltage

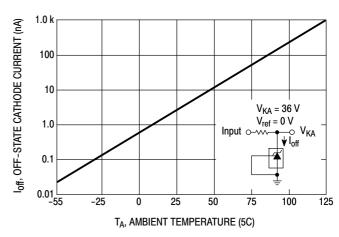


Figure 9. Off-State Cathode Current versus Ambient Temperature

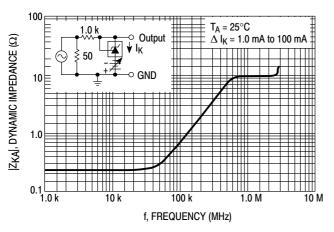


Figure 10. Dynamic Impedance versus Frequency

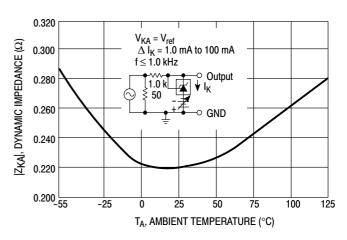


Figure 11. Dynamic Impedance versus Ambient Temperature

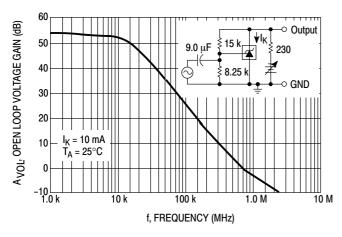


Figure 12. Open-Loop Voltage Gain versus Frequency

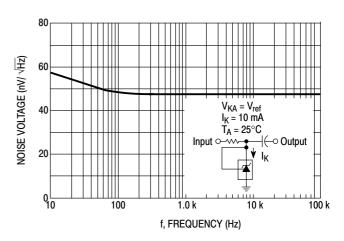


Figure 13. Spectral Noise Density

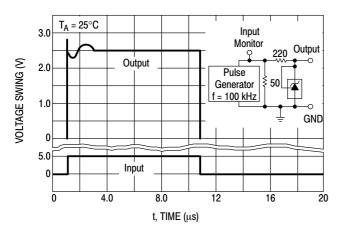


Figure 14. Pulse Response

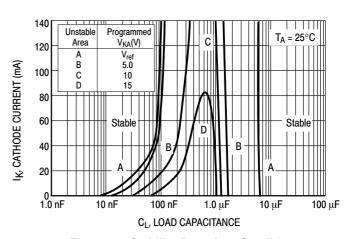


Figure 15. Stability Boundary Conditions

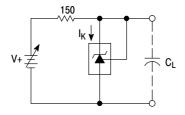


Figure 16. Test Circuit For Curve A of Stability Boundary Conditions

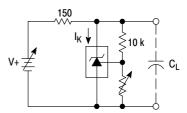


Figure 17. Test Circuit For Curves B, C, And D of Stability Boundary Conditions

TYPICAL APPLICATIONS

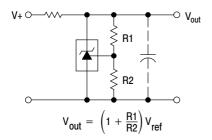


Figure 18. Shunt Regulator

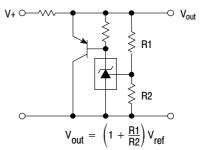


Figure 19. High Current Shunt Regulator

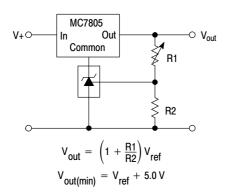


Figure 20. Output Control for a Three-Terminal Fixed Regulator

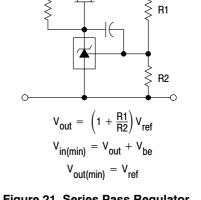


Figure 21. Series Pass Regulator

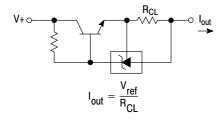


Figure 22. Constant Current Source

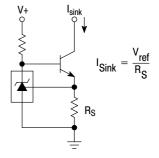


Figure 23. Constant Current Sink

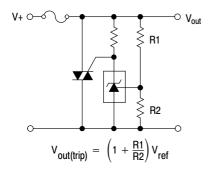


Figure 24. TRIAC Crowbar

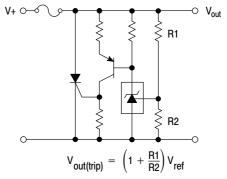
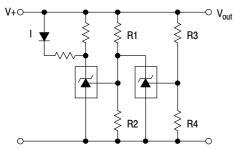


Figure 25. SRC Crowbar



L.E.D. indicator is 'on' when V+ is between the upper and lower limits.

$$\begin{aligned} \text{Lower Limit} &= \left(1 + \frac{R1}{R2}\right) V_{ref} \\ \text{Upper Limit} &= \left(1 + \frac{R3}{R4}\right) V_{ref} \end{aligned}$$

Figure 26. Voltage Monitor

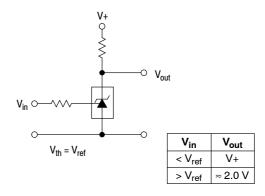


Figure 27. Single–Supply Comparator with Temperature–Compensated Threshold

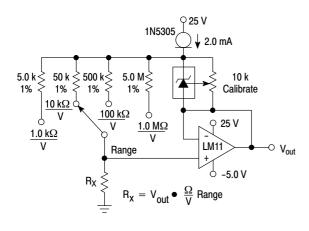


Figure 28. Linear Ohmmeter

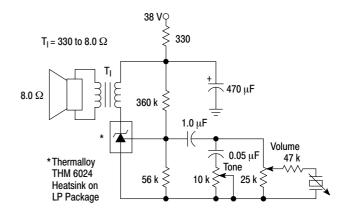


Figure 29. Simple 400 mW Phono Amplifier

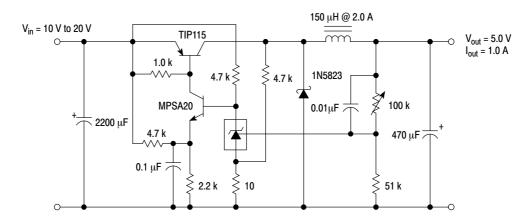


Figure 30. High Efficiency Step-Down Switching Converter

Test	Conditions	Results
Line Regulation	$V_{in} = 10 \text{ V to } 20 \text{ V}, I_0 = 1.0 \text{ A}$	53 mV (1.1%)
Load Regulation	V _{in} = 15 V, I _o = 0 A to 1.0 A	25 mV (0.5%)
Output Ripple	V _{in} = 10 V, I _o = 1.0 A	50 mVpp P.A.R.D.
Output Ripple	$V_{in} = 20 \text{ V}, I_0 = 1.0 \text{ A}$	100 mVpp P.A.R.D.
Efficiency	V _{in} = 15 V, I _o = 1.0 A	82%

APPLICATIONS INFORMATION

The TL431 is a programmable precision reference which is used in a variety of ways. It serves as a reference voltage in circuits where a non-standard reference voltage is needed. Other uses include feedback control for driving an optocoupler in power supplies, voltage monitor, constant current source, constant current sink and series pass regulator. In each of these applications, it is critical to maintain stability of the device at various operating currents and load capacitances. In some cases the circuit designer can estimate the stabilization capacitance from the stability boundary conditions curve provided in Figure 15. However, these typical curves only provide stability information at specific cathode voltages and at a specific load condition. Additional information is needed to determine the capacitance needed to optimize phase margin or allow for process variation.

A simplified model of the TL431 is shown in Figure 31. When tested for stability boundaries, the load resistance is 150 Ω . The model reference input consists of an input transistor and a dc emitter resistance connected to the device anode. A dependent current source, Gm, develops a current whose amplitude is determined by the difference between the 1.78 V internal reference voltage source and the input transistor emitter voltage. A portion of Gm flows through compensation capacitance, C_{P2} . The voltage across C_{P2} drives the output dependent current source, Go, which is connected across the device cathode and anode.

Model component values are:

 $V_{ref} = 1.78 \text{ V}$

 $Gm = 0.3 + 2.7 \exp(-I_C/26 \text{ mA})$

where I_C is the device cathode current and Gm is in mhos

Go =
$$1.25 (V_{cp}2) \mu mhos$$
.

Resistor and capacitor typical values are shown on the model. Process tolerances are $\pm 20\%$ for resistors, $\pm 10\%$ for capacitors, and $\pm 40\%$ for transconductances.

An examination of the device model reveals the location of circuit poles and zeroes:

P1 =
$$\frac{1}{2\pi R_{GM} C_{P1}}$$
 = $\frac{1}{2\pi * 1.0 M * 20 pF}$ = 7.96 kHz

$$P2 = \frac{1}{2\pi R_{P2}C_{P2}} = \frac{1}{2\pi*10 M*0.265 pF} = 60 \text{ kHz}$$

$$Z1 = \frac{1}{2\pi R_{71}C_{P1}} = \frac{1}{2\pi * 15.9 k * 20 pF} = 500 kHz$$

In addition, there is an external circuit pole defined by the load:

$$P_L = \frac{1}{2\pi R_I C_I}$$

Also, the transfer dc voltage gain of the TL431 is:

$$G = G_M R_{GM} GoR_L$$

Example 1:

 $\rm I_{\mbox{\scriptsize C}} = 10\,m\mbox{\scriptsize mA}, R_{\mbox{\scriptsize L}} = \,230\,\Omega, C_{\mbox{\scriptsize L}} = \,0.$ Define the transfer gain .

The DC gain is:

$$G = G_M R_{GM} GoR_L =$$
(2.138)(1.0 M)(1.25 μ)(230) = 615 = 56 dB

Loop gain =
$$G \frac{8.25 \text{ k}}{8.25 \text{ k} + 15 \text{ k}} = 218 = 47 \text{ dB}$$

The resulting transfer function Bode plot is shown in Figure 32. The asymptotic plot may be expressed as the following equation:

$$Av = 615 \frac{\left(1 + \frac{jf}{500 \text{ kHz}}\right)}{\left(1 + \frac{jf}{8.0 \text{ kHz}}\right)\left(1 + \frac{jf}{60 \text{ kHz}}\right)}$$

The Bode plot shows a unity gain crossover frequency of approximately 600 kHz. The phase margin, calculated from the equation, would be 55.9 degrees. This model matches the Open–Loop Bode Plot of Figure 12. The total loop would have a unity gain frequency of about 300 kHz with a phase margin of about 44 degrees.

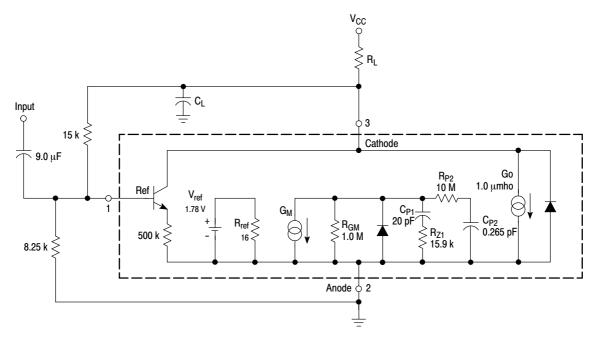


Figure 31. Simplified TL431 Device Model

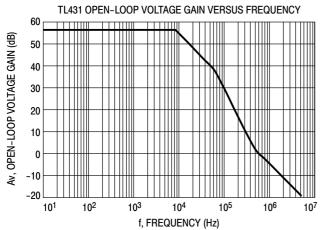


Figure 32. Example 1 Circuit Open Loop Gain Plot Example 2.

 I_C = 7.5 mA, R_L = 2.2 k Ω , C_L = 0.01 μ F. Cathode tied to reference input pin. An examination of the data sheet stability boundary curve (Figure 15) shows that this value of load capacitance and cathode current is on the boundary. Define the transfer gain.

The DC gain is:

$$G = G_M R_{GM} GoR_L =$$

 $(2.323)(1.0 \text{ M})(1.25 \mu)(2200) = 6389 = 76 \text{ dB}$

The resulting open loop Bode plot is shown in Figure 33. The asymptotic plot may be expressed as the following equation:

$$Av = 615 \frac{\left(1 + \frac{jf}{500 \text{ kHz}}\right)}{\left(1 + \frac{jf}{8.0 \text{ kHz}}\right)\!\left(1 + \frac{jf}{60 \text{ kHz}}\right)\!\left(1 + \frac{jf}{7.2 \text{ kHz}}\right)}$$

Note that the transfer function now has an extra pole formed by the load capacitance and load resistance.

Note that the crossover frequency in this case is about 250 kHz, having a phase margin of about -46 degrees. Therefore, instability of this circuit is likely.

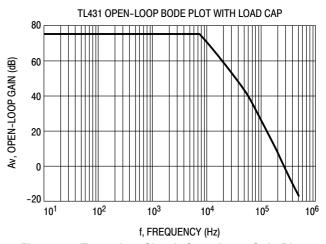


Figure 33. Example 2 Circuit Open Loop Gain Plot

With three poles, this system is unstable. The only hope for stabilizing this circuit is to add a zero. However, that can only be done by adding a series resistance to the output capacitance, which will reduce its effectiveness as a noise filter. Therefore, practically, in reference voltage applications, the best solution appears to be to use a smaller value of capacitance in low noise applications or a very large value to provide noise filtering and a dominant pole rolloff of the system.

ORDERING INFORMATION

Device	Marking Code	Operating Temperature Range	Package Code	Shipping Information [†]	Tolerance
TL431ACDG	AC				1.0%
TL431BCDG	BC		SOIC-8 (Pb-Free)	98 Units / Rail	0.4%
TL431CDG	С		(1.5.1.00)		2.2%
TL431ACDR2G	AC		0010.5		1.0%
TL431BCDR2G	BC		SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	0.4%
TL431CDR2G	С		(1.5.1.00)		2.2%
TL431ACDMR2G	TAC		14: 0		1.0%
TL431BCDMR2G	TBC		Micro8 (Pb-Free)	4000 Units / Tape & Reel	0.4%
TL431CDMR2G	T-C		(. 2)		2.2%
TL431ACPG	ACP		DDID 0		1.0%
TL431BCPG	BCP		PDIP-8 (Pb-Free)	50 Units / Rail	0.4%
TL431CPG	CP		(. 2)		2.2%
TL431ACLPG	ACLP	0°C to 70°C	TO 00		1.0%
TL431BCLPG	BCLP	0 0 10 70 0	TO-92 (Pb-Free)	2000 Units / Bag	0.4%
TL431CLPG	CLP		(. 2 1100)		2.2%
TL431ACLPRAG	ACLP				1.0%
TL431BCLPRAG	BCLP				0.4%
TL431CLPRAG	CLP		TO-92	2000 Unito / Tana & Roal	2.2%
TL431ACLPREG	ACLP		(Pb-Free)	2000 Units / Tape & Reel	1.0%
TL431BCLPREG	BCLP				0.4%
TL431CLPREG	CLP				2.2%
TL431ACLPRPG	ACLP		TO-92 (Pb-Free)	2000 / Tape & Ammo Box	1.0%
TL431BCLPRMG	BCLP		TO 00		0.4%
TL431CLPRMG	CLP		TO-92 (Pb-Free)	2000 Units / Fan-Fold	2.2%
TL431CLPRPG	CLP		(. 2		2.2%
TL431AIDG	Al		0010.0		1.0%
TL431BIDG	Bl		SOIC-8 (Pb-Free)	98 Units / Rail	0.4%
TL431IDG	1		(* 2 * 1 * 2 * 7		2.2%
TL431AIDR2G	Al		0010.0		1.0%
TL431BIDR2G	Bl		SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	0.4%
TL431IDR2G	ļ		,		2.2%
TL431AIDMR2G	TAI		MioreO		1.0%
TL431BIDMR2G	TBI		Micro8 (Pb-Free)	4000 Units / Tape & Reel	0.4%
TL431IDMR2G	T–I		,		2.2%
TL431AIPG	AIP		DDID 0		1.0%
TL431BIPG	BIP	−40°C to 85°C	PDIP-8 (Pb-Free)	50 Units / Rail	0.4%
TL431IPG	IP	10 0 10 00 0	,		2.2%
TL431AILPG	AILP		TO-92		1.0%
TL431BILPG	BILP		(Pb-Free)	2000 Units / Bag	0.4%
TL431ILPG	ILP		,		2.2%
TL431AILPRAG	AILP				1.0%
TL431BILPRAG	BILP		TO-92	2000 Units / Tape & Reel	0.4%
SC431ILPRAG	ILP		(Pb-Free)	2000 Office, Tape a rice	2.2%
TL431ILPRAG	ILP				2.2%
TL431AILPRMG	AILP		TO 00		1.0%
TL431AILPRPG			TO-92 (Pb-Free)	2000 / Tape & Ammo Box	1.0%
TL431ILPRPG	ILP		, ,		2.2%

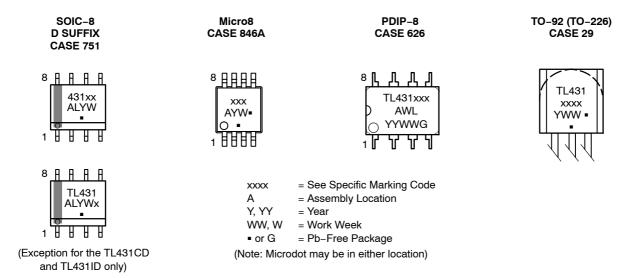
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ORDERING INFORMATION

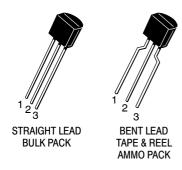
Device	Marking Code	Operating Temperature Range	Package Code	Shipping Information [†]	Tolerance
TL431BVDG	BV		SOIC-8	98 Units / Rail	0.4%
TL431BVDR2G	DV		(Pb-Free)	2500 Units / Tape & Reel	0.4%
TL431BVDMR2G	TBV		Micro8 (Pb-Free)	4000 Units / Tape & Reel	0.4%
TL431BVLPG	BVLP		TO-92	2000 Units / Bag	0.4%
TL431BVLPRAG	DVLF		(Pb-Free)	2000 Units / Tape & Reel	0.4%
TL431BVPG	BVP	−40°C to 125°C	PDIP-8 (Pb-Free)	50 Units / Rail	0.4%
NCV431AIDMR2G	RAN		Micro8 (Pb-Free)	4000 Units / Tape & Reel	1%
NCV431AIDR2G	AV		SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	1%
NCV431BVDMR2G	NVB		Micro8 (Pb-Free)	4000 Units / Tape & Reel	0.4%
NCV431BVDR2G	BV		SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	0.4%

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

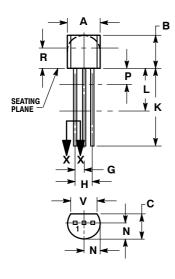
MARKING DIAGRAMS



PACKAGE DIMENSIONS



TO-92 (TO-226) CASE 29-11 **ISSUE AM**



STRAIGHT LEAD **BULK PACK**



- NOTES:

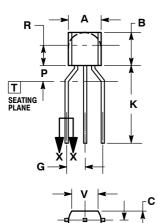
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

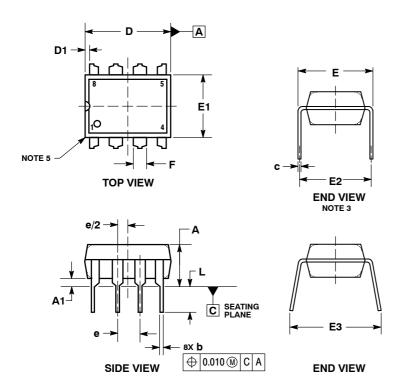
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS						
DIM	MIN	MAX					
Α	4.45	5.20					
В	4.32	5.33					
С	3.18	4.19					
D	0.40	0.54					
G	2.40	2.80					
J	0.39	0.50					
K	12.70						
N	2.04	2.66					
P	1.50	4.00					
R	2.93						
V	3.43						

PACKAGE DIMENSIONS

PDIP-8 **P SUFFIX** CASE 626-05 **ISSUE M**

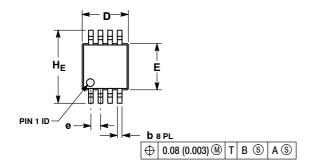


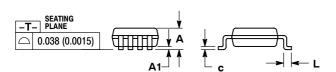
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: INCHES.
 3. DIMENSION E IS MEASURED WITH THE LEADS RESTRAINED PARALLEL AT WIDTH E2.
 4. DIMENSION E1 DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

		INCHES	;	MIL	LIMETE	RS
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			0.210			5.33
A1	0.015			0.38		
b	0.014	0.018	0.022	0.35	0.46	0.56
С	0.008	0.010	0.014	0.20	0.25	0.36
D	0.355	0.365	0.400	9.02	9.27	10.02
D1	0.005			0.13		
E	0.300	0.310	0.325	7.62	7.87	8.26
E1	0.240	0.250	0.280	6.10	6.35	7.11
E2	(0.300 BS	С		7.62 BSC)
E3			0.430			10.92
е	0.100 BSC			•	2.54 BSC)
L	0.115	0.130	0.150	2.92	3.30	3.81

PACKAGE DIMENSIONS

Micro8 **DM SUFFIX** CASE 846A-02 **ISSUE G**



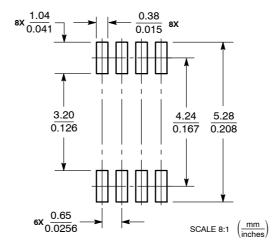


- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. 846A-01 OBSOLETE, NEW STANDARD 846A-02.

	М	ILLIMETE	RS		INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.05	0.08	0.15	0.002	0.003	0.006
b	0.25	0.33	0.40	0.010	0.013	0.016
С	0.13	0.18	0.23	0.005	0.007	0.009
D	2.90	3.00	3.10	0.114	0.118	0.122
E	2.90	3.00	3.10	0.114	0.118	0.122
е	0.65 BSC			0.026 BSC)	
L	0.40	0.55	0.70	0.016	0.021	0.028
He	4 75	4 90	5.05	0.187	0.193	0.199

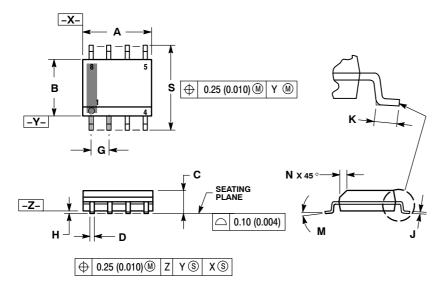
SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOIC-8 **D SUFFIX** CASE 751-07 **ISSUE AK**

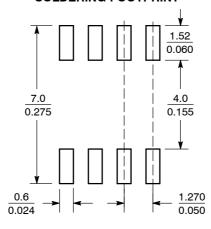


NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
၁	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
Ĺ	0.19	0.25	0.007	0.010
Κ	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
s	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



mm SCALE 6:1

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